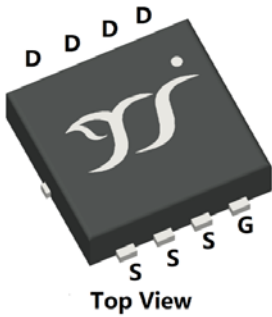
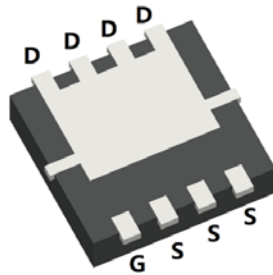




N-Channel Enhancement Mode Field Effect Transistor

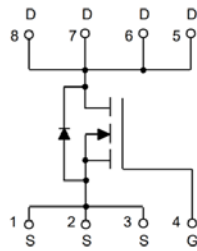


Top View



Bottom View

PDFN3333-8L



Product Summary

• V_{DS}	30V
• I_D	84A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	$<4m\Omega$
• $R_{DS(ON)}$ (at $V_{GS}=4.5V$)	$<9.7m\Omega$
• 100% EAS Tested	
• 100% ∇V_{DS} Tested	
• ESD Level(HBM)	H1B

General Description

- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- PD SR-MOS
- Electric-powered tools

■ Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			V _{DS}	-	30	V
Gate-source Voltage			V _{GS}	-20	20	
Continuous Drain Current (Note 1,2)	Steady-State	T _A =25°C,V _{GS} =10V	I _D	-	17.5	A
		T _A =100°C,V _{GS} =10V		-	11.1	
Continuous Drain Current (Note 1,3)	Steady-State	T _C =25°C,V _{GS} =10V,Chip limitation		-	84	
		T _C =100°C,V _{GS} =10V		-	53	
Pulsed Drain Current	T _C =25°C,t _p ≤10μs		I _{DM}	-	336	
Maximum Body-Diode Continuous Current	T _C =25°C		I _S		40	
Avalanche Energy (non-repetitive)	T _J =25°C,V _G =10V,R _G =25Ω,L=0.5mH,I _{AS} =21.7A		EAS	-	117.7	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T _A =25°C	P _D	-	2	W
		T _A =100°C		-	0.83	
Total Power Dissipation (Note 1,3)	Steady-State	T _C =25°C		-	48	
		T _C =100°C		-	19	
Junction and Storage Temperature Range			T _J ,T _{STG}	-55	150	°C

■ Thermal Resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	-	60	$^{\circ}C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	-	2.6	



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■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA, T _j =25°C	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V, T _j =25°C	-	-	1	μA
		V _{DS} =30V, V _{GS} =0V, T _j =125°C	-	-	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V, T _j =25°C	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA, T _j =25°C	1	1.5	2	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A, T _j =25°C	-	3.2	4	mΩ
		V _{GS} =4.5V, I _D =10A, T _j =25°C	-	6.5	9.7	mΩ
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V, T _j =25°C	-	0.83	1.2	V
Gate Resistance	R _G	f=1MHz, T _j =25°C	-	2.3	-	Ω
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz, T _j =25°C	-	2298	-	pF
Output Capacitance	C _{oss}		-	318	-	
Reverse Transfer Capacitance	C _{rss}		-	280	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =20A, T _j =25°C	-	44	-	nC
Gate-Source Charge	Q _{gs}		-	8	-	
Gate-Drain Charge	Q _{gd}		-	9	-	
Reverse Recovery Charge	Q _{rr}	I _F =20A, di/dt=100A/μs, V _{GS} =0V, V _R =15V, T _j =25°C	-	10	-	nC
Reverse Recovery Time	t _{rr}		-	17	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =15V, I _D =20A, R _{GEN} =3Ω, T _j =25°C	-	10.5	-	ns
Turn-on Rise Time	t _r		-	36	-	
Turn-off Delay Time	t _{D(off)}		-	37	-	
Turn-off Fall Time	t _f		-	17	-	

Note:

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of 150 $^\circ C$. The value in any given application depends on the user's specific board design.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).



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■ Typical Electrical and Thermal Characteristics Diagrams

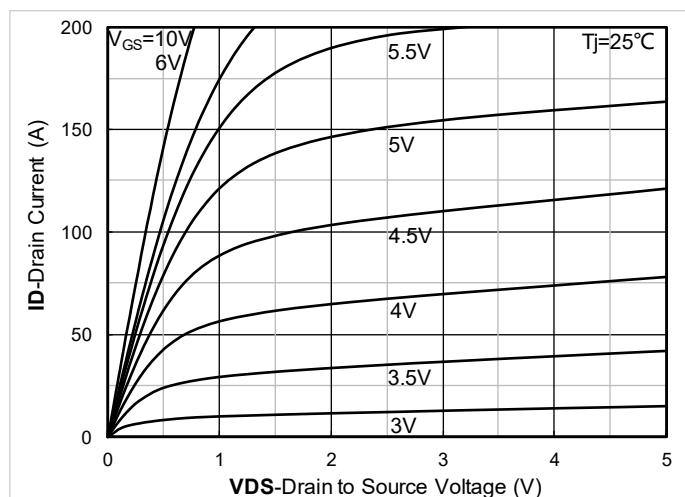


Figure 1. Output Characteristics; typical values

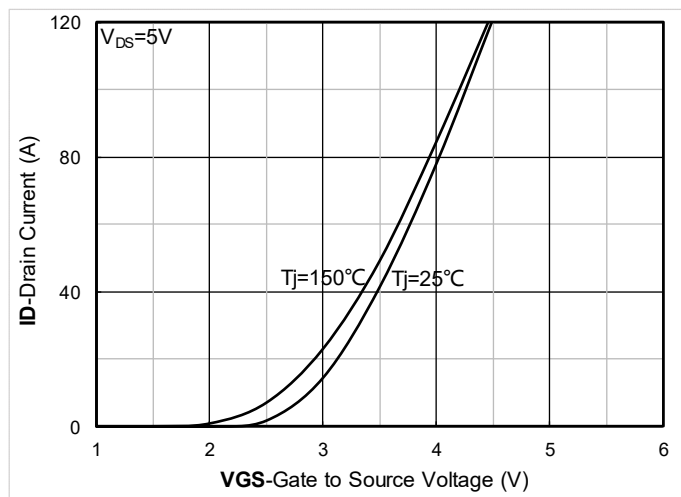


Figure 2. Transfer Characteristics; typical values

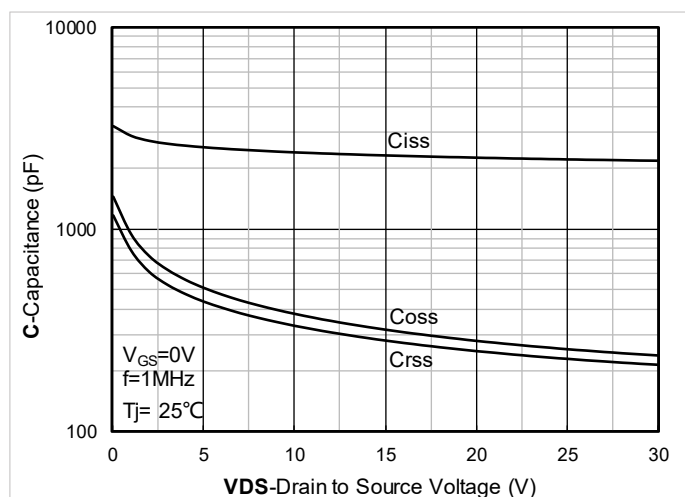


Figure 3. Capacitance Characteristics; typical values

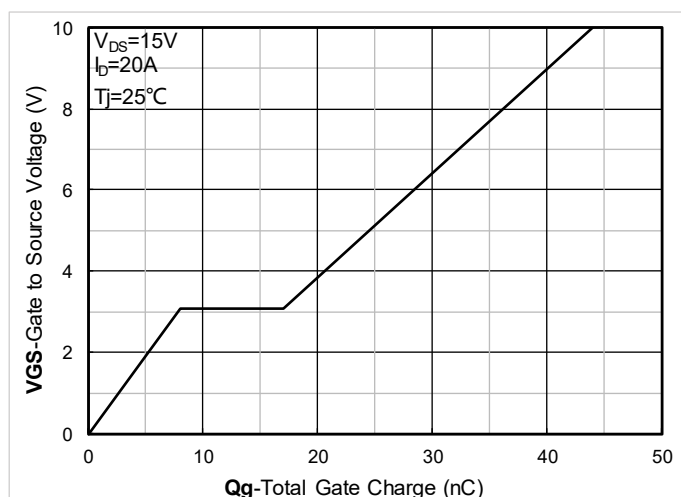


Figure 4. Gate Charge; typical values

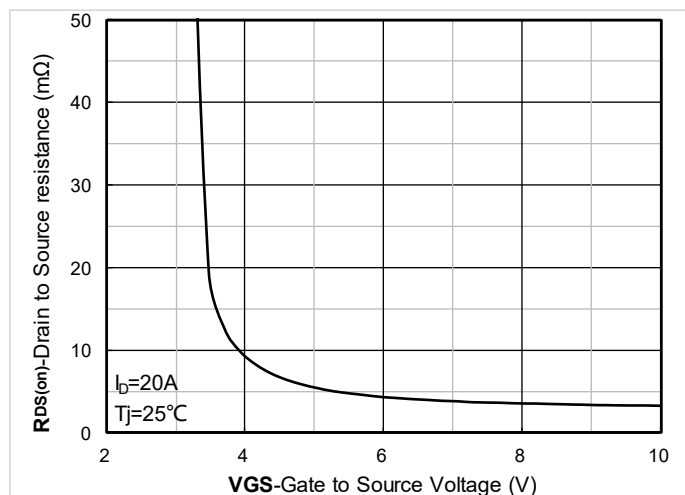


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

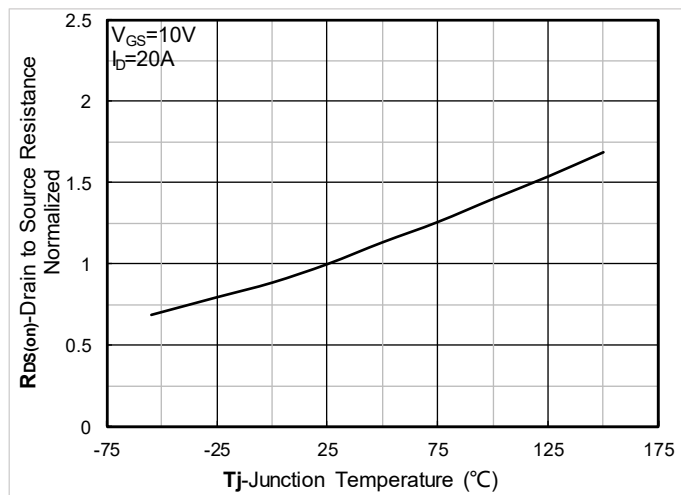


Figure 6. Normalized On-Resistance

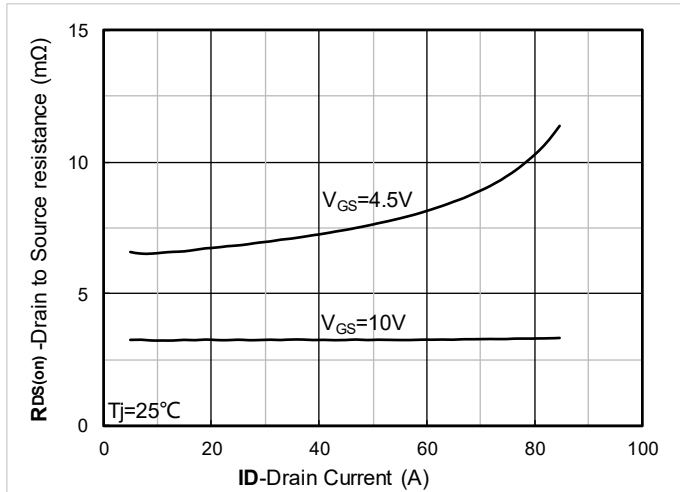


Figure 7. $R_{DS(on)}$ vs. Drain Current; typical values

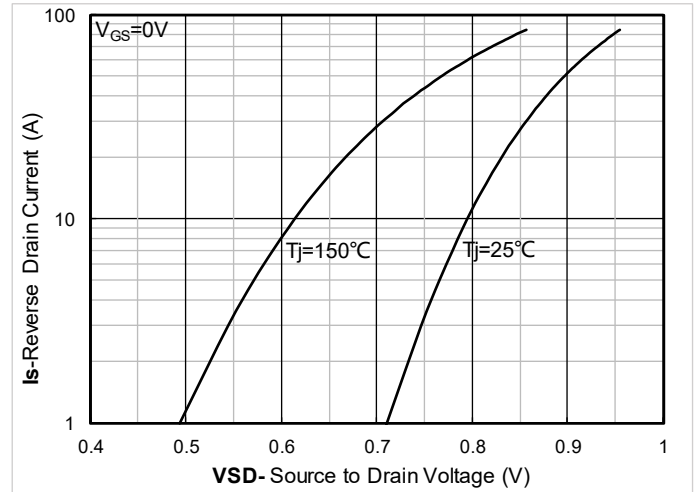


Figure 8. Forward characteristics of reverse diode; typical values

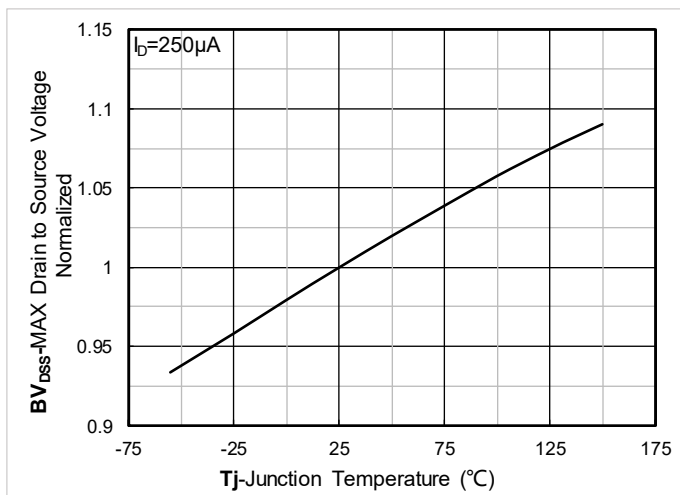


Figure 9. Normalized breakdown voltage

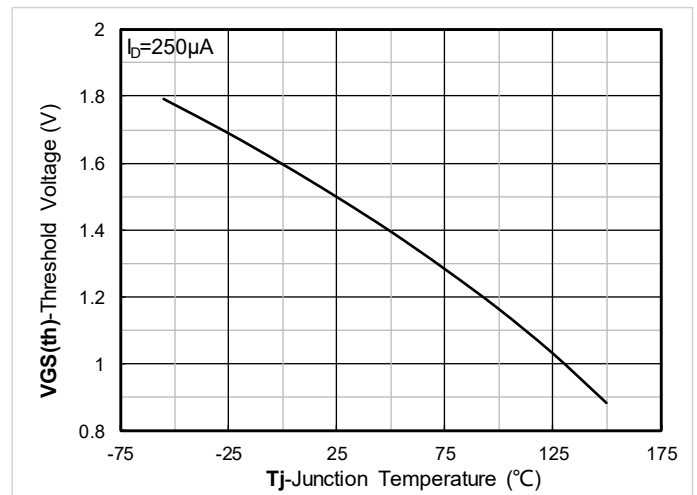


Figure 10. Gate Threshold voltage; typical values

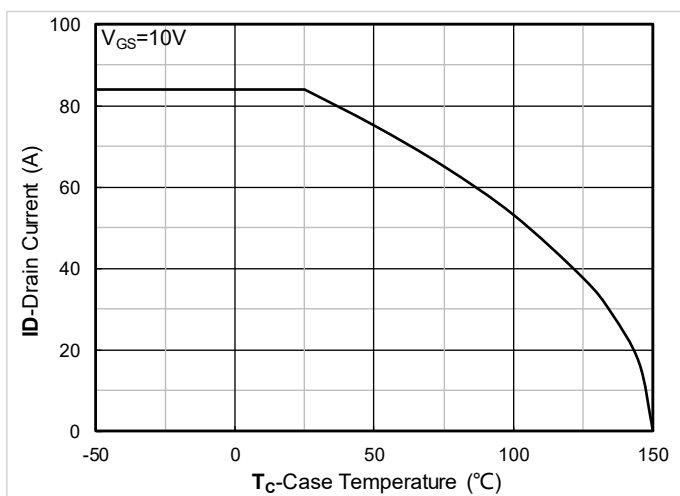


Figure 11. Current dissipation

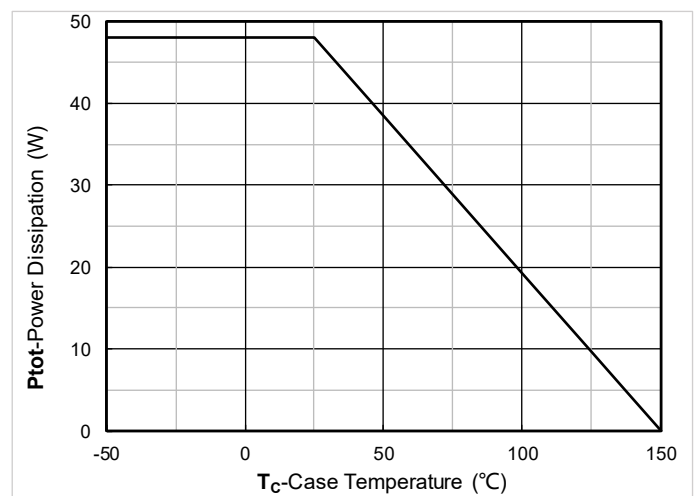


Figure 12. Power dissipation

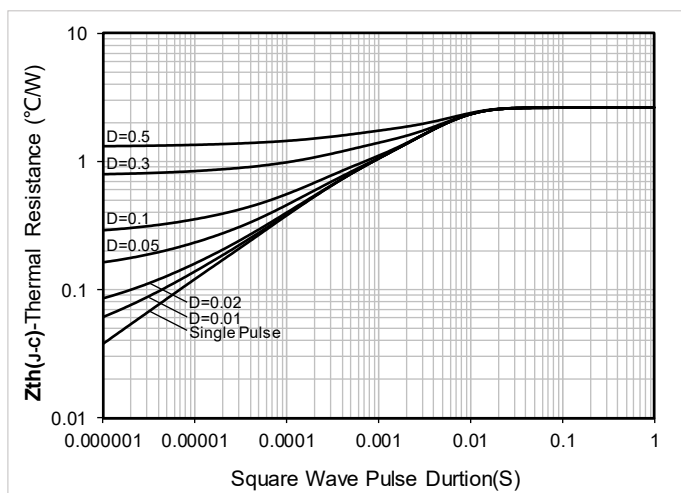


Figure 13. Maximum Transient Thermal Impedance

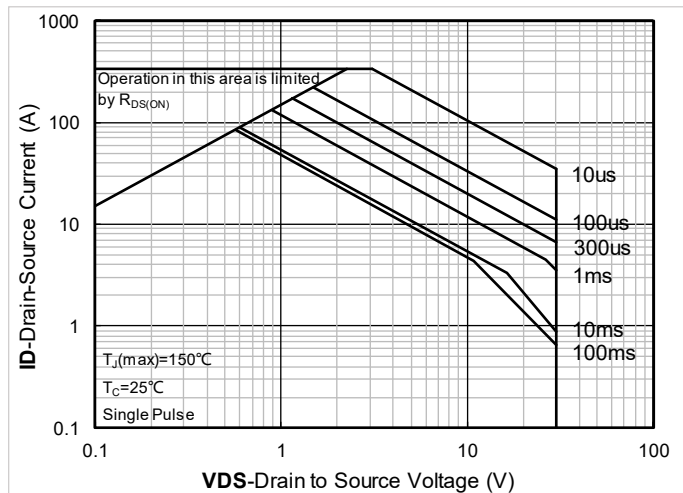


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

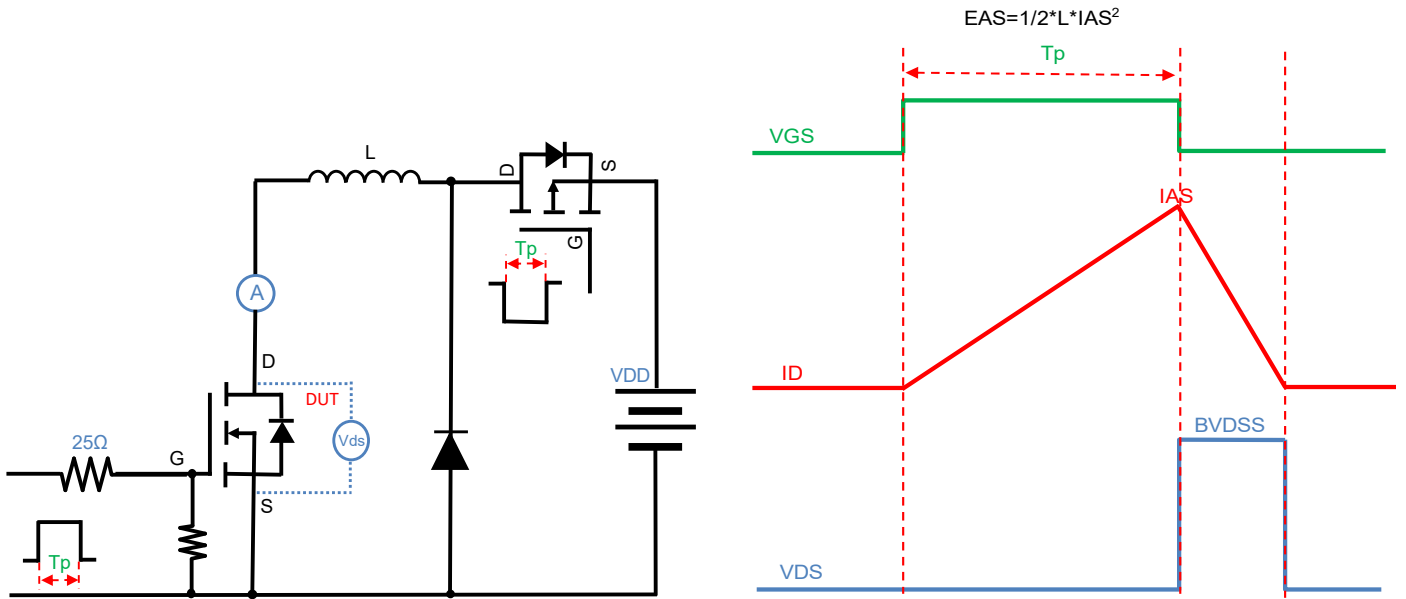


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

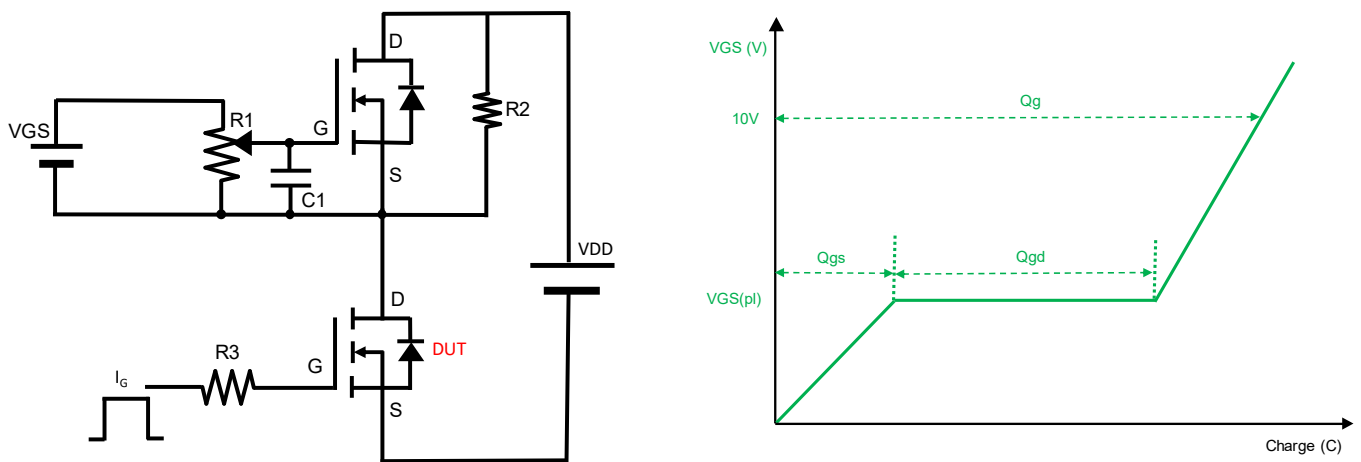


Figure B. Gate Charge Test Circuit & Waveform

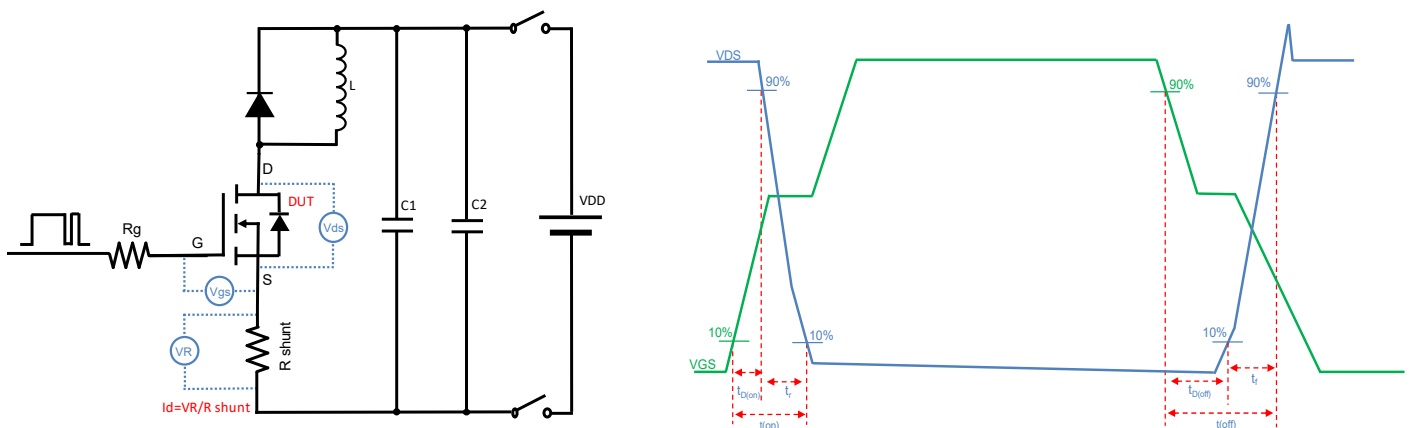


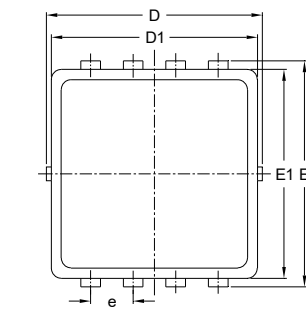
Figure C. Resistive Switching Test Circuit & Waveform



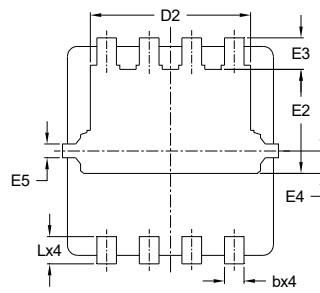


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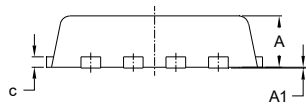
■ PDFN3333-8L-B-0.75mm Package information



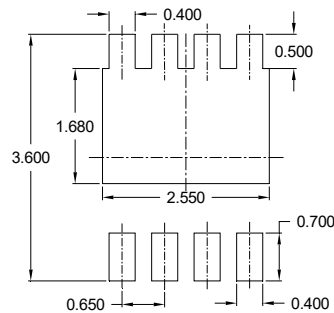
TOP VIEW



BOTTOM VIEW



SIDE VIEW



SUGGESTED SOLDER PAD LAYOUT

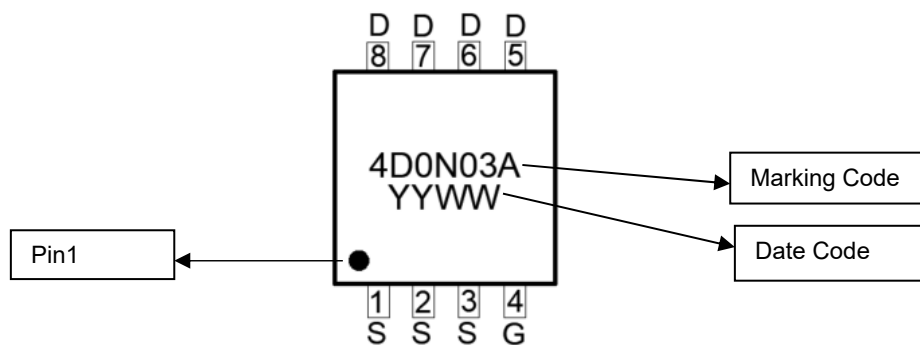
SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.028	0.033	0.700	0.850
A1	0.000	0.002	0.000	0.050
b	0.008	0.016	0.200	0.400
c	0.004	0.010	0.100	0.250
D	0.124	0.136	3.150	3.450
D1	0.118	0.130	3.000	3.300
D2	0.089	0.104	2.250	2.650
E	0.124	0.136	3.150	3.450
E1	0.114	0.126	2.900	3.200
E2	0.052	0.068	1.320	1.720
E3	0.011	0.026	0.280	0.650
E4	0.013 REF		0.330 REF	
E5	0.008 REF		0.200 REF	
e	0.026 BSC		0.650 BSC	
L	0.012	0.020	0.300	0.500

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

UNIT: mm

■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. 4D0N03A is marking code, YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



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